

این دیتاشیت توسط توکل الکترونیک تهیه و ارائه شده است.
جهت مشاهده قیمت، موجودی و ثبت سفارش این قطعه به وبسایت توکل الکترونیک مراجعه فرمایید.



مشاهده قیمت و خرید

برای خرید و مشاهده سایر محصولات کلیک کنید



MOS FIELD EFFECT POWER TRANSISTORS 2SK2134, 2SK2134-Z

SWITCHING
N-CHANNEL POWER MOS FET
INDUSTRIAL USE

DESCRIPTION

The 2SK2134, 2SK2134-Z are N-channel Power MOS Field Effect Transistors designed for high voltage switching applications.

FEATURES

- Low On-state Resistance
 $R_{DS(on)} = 0.4 \Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 7.0 \text{ A)}$
- Low C_{iss} $C_{iss} = 500 \text{ pF TYP.}$
- High Avalanche Capability Ratings

QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS

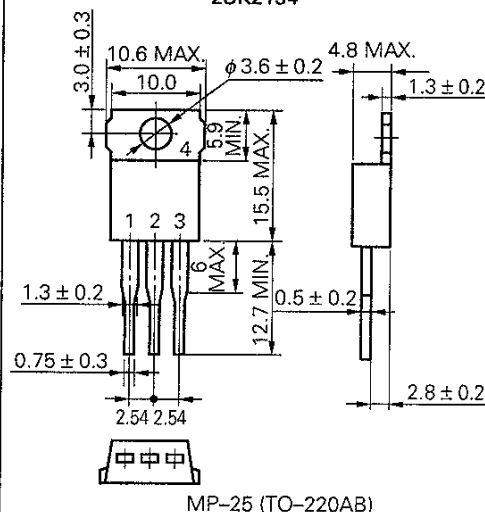
Drain to Source Voltage	V_{DS}	200	V
Gate to Source Voltage	V_{GSS}	± 30	V
Drain Current (DC)	$I_{D(DS)}$	± 13	A
Drain Current (pulse)	$I_{D(pulse)^*}$	± 39	A
Single Avalanche Current**	I_{AS}	13	A
Single Avalanche Energy**	E_{AS}	33.8	mJ
Total Power Dissipation ($T_a = 25^\circ\text{C}$)	P_{T1}	1.5	W
Total Power Dissipation ($T_c = 25^\circ\text{C}$)	P_{T2}	70	W
Storage Temperature	T_{stg}	$-55 \text{ to } +150$	$^\circ\text{C}$
Channel Temperature	T_{ch}	150	$^\circ\text{C}$

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

** Starting $T_{ch} = 25^\circ\text{C}$, $R_G = 25 \Omega$, $V_{GS} = 20 \text{ V} \rightarrow 0$

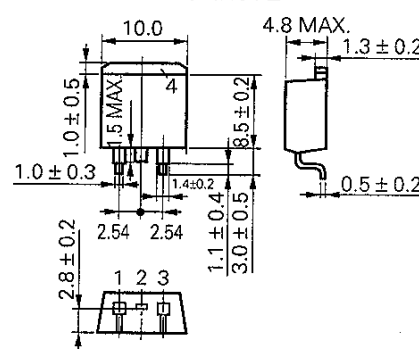
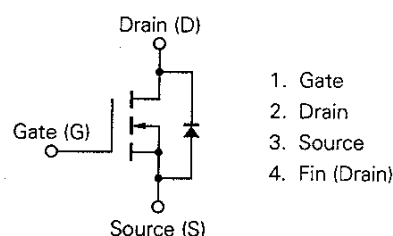
PACKAGE DIMENSIONS (Unit : mm)

2SK2134



MP-25 (TO-220AB)

2SK2134-Z



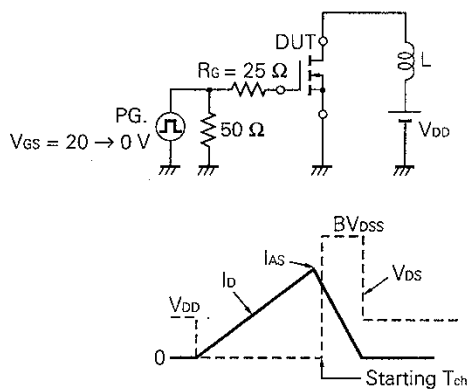
1. Gate
2. Drain
3. Source
4. Fin (Drain)

(Diode in the figure is the parasitic diode)

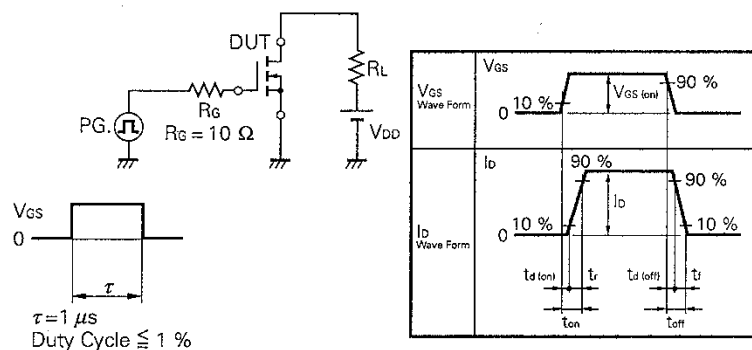
ELECTRICAL CHARACTERISTICS ($T_a = 25\text{ }^{\circ}\text{C}$)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-state Resistance	$R_{DS(on)}$		0.3	0.4	Ω	$V_{GS} = 10\text{ V}$, $I_D = 7.0\text{ A}$
Gate to Source Cutoff Voltage	$V_{GS(off)}$	2.0		4.0	V	$V_{DS} = 10\text{ V}$, $I_D = 1\text{ mA}$
Forward Transfer Admittance	$ y_{fs} $	2.0			S	$V_{DS} = 10\text{ V}$, $I_D = 7.0\text{ A}$
Drain Leakage Current	I_{DSS}			100	μA	$V_{DS} = 200\text{ V}$, $V_{GS} = 0$
Gate to Source Leakage Current	I_{GSS}			± 100	nA	$V_{GS} = \pm 30\text{ V}$, $V_{DS} = 0$
Input Capacitance	C_{iss}		500		pF	$V_{DS} = 10\text{ V}$ $V_{GS} = 0$ $f = 1\text{ MHz}$
Output Capacitance	C_{oss}		230		pF	
Reverse Transfer Capacitance	C_{rss}		60		pF	
Turn-On Delay Time	$t_d(on)$		12		ns	$V_{GS} = 10\text{ V}$ $V_{DD} = 100\text{ V}$ $I_D = 7.0\text{ A}$, $R_G = 10\text{ }\Omega$ $R_L = 14.3\text{ }\Omega$
Rise Time	t_r		45		ns	
Turn-Off Delay Time	$t_d(off)$		35		ns	
Fall Time	t_f		12		ns	
Total Gate Charge	Q_G		15		nC	$V_{GS} = -10\text{ V}$ $I_D = 13\text{ A}$ $V_{DD} = 160\text{ V}$
Gate to Source Charge	Q_{GS}		5.0		nC	
Gate to Drain Charge	Q_{GD}		8.0		nC	
Diode Forward Voltage	$V_{F(S-D)}$		1.0		V	$I_F = 13\text{ A}$, $V_{GS} = 0$
Reverse Recovery Time	t_{rr}		200		ns	$I_F = 13\text{ A}$ $di/dt = 50\text{ A}/\mu\text{s}$
Reverse Recovery Charge	Q_{rr}		0.6		μC	

Test Circuit 1 : Avalanche Capability



Test Circuit 2 : Switching Time



Test Circuit 3 : Gate Charge

